

10/510455

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TI: Transfer mold-type **power semiconductor module** for inverter, has **power terminal** connected to **power circuit**, that is bent twice so that it is initially **separated** from metal base and then extends along upward direction

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AB: NOVELTY - A **power terminal** (12) connected to **power circuit**, is bent twice such that it is initially **separated** from the metal base in the **module**, and then extends along upward direction. A control terminal (13) connected to control circuit section, is bent at right angle after it is extracted out from the **module**.; USE - **Power semiconductor module** such as insulated gate bipolar transistor **module** for electric **power** converters like inverter. ADVANTAGE - Provides **power semiconductor module** which is highly efficient and small in size. As the lead frame is effectively used and need for new control terminal is avoided, manufacturing cost is reduced. DESCRIPTION OF DRAWING(S) - The figure shows the sectional view of **power semiconductor module**. **Power terminal** 12 **Control terminal** 13

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